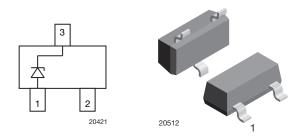
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Single-Line ESD Protection in SOT-23



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MARKING (example only)



YYY = type code (see table below) XX = date code

FEATURES

- Single-line ESD-protection device
- ESD-protection acc. IEC 61000-4-2 ± 30 kV contact discharge ± 30 kV air discharge
- ESD capability according to AEC-Q101: human body model: class H3B: > 8 kV
- Space saving SOT-23 package
- e3 Sn
- AEC-Q101 qualified available
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

ORDERIN	ORDERING INFORMATION									
	ENVIR	ONMENTAL AN	ID QUALITY CO	DDE	PACKAG	ING CODE				
PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED				3K PER 7" REEL (8 mm TAPE),	10K PER 13" REEL (8 mm TAPE),	ORDERING CODE (EXAMPLE)			
()	QUALIFIED	STANDARD			15K/BOX = MOQ	10K/BOX = MOQ				
GSOT05-		E		3	-08		GSOT05-E3-08			
GSOT05-			G	3	-08		GSOT05-G3-08			
GSOT05-	Н	E		3	-08		GSOT05-HE3-08			
GSOT05-	Н		G	3	-08		GSOT05-HG3-08			
GSOT05-		E		3		-18	GSOT05-E3-18			
GSOT05-			G	3		-18	GSOT05-G3-18			
GSOT05-	Н	E		3		-18	GSOT05-HE3-18			
GSOT05-	Н		G	3		-18	GSOT05-HG3-18			

PACKA		L					
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS
GSOT03	SOT-23	03	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
000100	001 20	03G	Green	8.1 mg	02 34 0 0	(according J-STD-020)	200 0/10 3 at terminais
GSOT04	SOT-23	04	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
000104	001 20	04G	Green	8.1 mg	02 34 0 0	(according J-STD-020)	
GSOT05	SOT-23	05	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
000100	001 20	05G	Green	8.1 mg		(according J-STD-020)	
GSOT08	SOT-23	08	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
030100	301-23	08G	Green	8.1 mg	02 94 0-0	(according J-STD-020)	200 0/10 3 at terminais
GSOT12	SOT-23	12	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
030112	301-23	12G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	200 C/TOS at terminais
GSOT15	SOT-23	15	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
000113	301-23	15G	Green	8.1 mg	02 94 0-0	(according J-STD-020)	200 0/10 3 at terminais
GSOT24	SOT-23	24	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
630124	301-23	24G	Green	8.1 mg	02 54 0-0	(according J-STD-020)	200 O/TO S at terminals
GSOT36	SOT-23	36	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
G30130	301-23	36G	Green	8.1 mg	0L 94 V-0	(according J-STD-020)	200 O/TO S at terminals

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1 For technical questions, contact: <u>ESDprotection@vishay.com</u> Document Number: 85807



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ABSOLUTE MAXIMUM RATINGS GSOT03							
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	30	А			
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	369	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV			
	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV			
Operating temperature	Junction temperature	TJ	-40 to +125	°C			
Storage temperature		T _{STG}	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS GSOT04							
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	30	А			
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	429	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV			
	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV			
Operating temperature	Junction temperature	TJ	-40 to +125	°C			
Storage temperature		T _{STG}	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS GSOT05							
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	30	А			
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	480	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	± 30	kV			
	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV			
Operating temperature	Junction temperature	TJ	-40 to +125	°C			
Storage temperature		T _{STG}	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS GSOT08						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	18	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	345	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV		
	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

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ABSOLUTE MAXIMUM RATINGS GSOT12						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	12	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	312	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT15							
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	8	А			
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	230	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV			
	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV			
Operating temperature	Junction temperature	TJ	-40 to +125	°C			
Storage temperature		T _{STG}	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS GSOT24						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	5	A		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	235	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT36						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	3.5	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	248	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV		
ESD Immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

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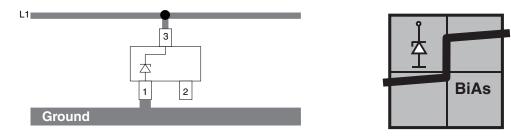
BIAs-MODE (1-line Bidirectional Asymmetrical protection mode)

With the GSOTxx one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 3 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified maximum reverse working voltage (V_{RWM}) the protection diode between pin 1 and pin 3 offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the breakdown voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The clamping voltage (V_C) is defined by the breakdown voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection diode.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction through the protection diode. The low forward voltage (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the GSOTxx clamping behavior is Bidirectional and Asymmetrical (BiAs).



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ELECTRICAL CHARACTERISTICS GSOT03 ($T_{amb} = 25$ °C unless otherwise specified) between pin 3 and pin 1								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	3.3	V		
Reverse voltage	at I _R = 100 μA	V _R	3.3	-	-	V		
Reverse current	at V _R = 3.3 V	I _R	-	-	100	μA		
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	4	4.6	5.5	V		
	at I _{PP} = 1 A	V	-	5.7	7.5	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	10	12.3	V		
	at I _{PP} = 1 A	N	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V		
2 II	at $V_R = 0 V$; f = 1 MHz	<u> </u>	-	420	600	pF		
Capacitance	at V _R = 1.6 V; f = 1 MHz	C _D	-	260	-	pF		

ELECTRICAL CHARACTERISTICS GSOT04 ($T_{amb} = 25$ °C unless otherwise specified) between pin 3 and pin 1							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines	
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	4	V	
Reverse voltage	at I _R = 20 μA	V _R	4	-	-	V	
Reverse current	at V _R = 4 V	I _R	-	-	20	μA	
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	5	6.1	7	V	

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GSOT03 to GSOT36



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ELECTRICAL CHARAC between pin 3 and pin 1	TERISTICS GSOT04 (T _{amb} = 25 °	°C unless ot	herwise s	pecified)		
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Reverse clamping voltage	at I _{PP} = 1 A	V	-	7.5	9	V
	at I _{PP} = I _{PPM} = 30 A	V _C	-	11.2	14.3	V
En estatuto de contra de la con	at I _{PP} = 1 A	V	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V
Osnasitanas	at $V_R = 0 V$; f = 1 MHz	6	-	310	450	pF
Capacitance	at V _R = 2 V; f = 1 MHz	C _D	-	200	-	pF

ELECTRICAL CHARACTERISTICS GSOT05 (T _{amb} = 25 °C unless otherwise s	specified)
between pin 3 and pin 1	

between pin e and pin i						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	5	V
Reverse voltage	at I _R = 10 μA	V _R	5	-	-	V
Reverse current	at V _R = 5 V	I _R	-	-	10	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	6	6.8	8	V
	at I _{PP} = 1 A	N	-	7	8.7	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	12	16	V
Forward elemping voltage	at I _{PP} = 1 A	V	-	1	1.2	V
Forward clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _F	-	4.5	-	V
	at $V_R = 0 V$; f = 1 MHz	_	-	260	350	pF
Capacitance	at $V_R = 2.5 V$; f = 1 MHz	C _D	-	150	-	pF

ELECTRICAL CHARACTERISTICS GSOT08 (T_{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1

between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	8	V
Reverse voltage	at I _R = 5 μA	V _R	8	-	-	V
Reverse current	at V _R = 8 V	I _R	-	-	5	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	9	10	11	V
Poweree elemping veltage	at I _{PP} = 1 A		-	10.7	13	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 18 A	V _C	-	15.2	19.2	V
Forward alamping voltage	at I _{PP} = 1 A	V	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 18 A	V _F	-	3	-	V
Conceitance	at $V_R = 0$ V; f = 1 MHz		-	160	250	pF
Capacitance	at V _R = 4 V; f = 1 MHz	C _D	-	80	-	pF

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GSOT03 to GSOT36



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PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	12	V
Reverse voltage	at I _R = 1 μA	V _R	12	-	-	V
Reverse current	at V _R = 12 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	13.5	15	16.5	V
Deverse elemping veltage	at I _{PP} = 1 A		-	15.4	18.7	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 12 A	V _C	-	21.2	26	V
	at I _{PP} = 1 A	N	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 12 A	V _F	-	2.2	-	V
0	at $V_R = 0 V$; f = 1 MHz	_	-	115	150	pF
Capacitance	at V _B = 6 V; f = 1 MHz	CD	-	50	-	pF

ELECTRICAL CHARACTERISTICS GSOT15 (T _{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines	
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	15	V	
Reverse voltage	at I _R = 1 µA	V _R	15	-	-	V	
Reverse current	at V _R = 15 V	I _R	-	-	1	μA	
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	16.5	18	20	V	
Povoroo olomping voltago	at I _{PP} = 1 A	V	-	19.4	23.5	V	
Reverse clamping voltage	at I _{PP} = I _{PPM} = 8 A	V _C	-	24.8	28.8	V	
Forward alamping voltage	at I _{PP} = 1 A	- V _F	-	1	1.2	V	
Forward clamping voltage	at I _{PP} = I _{PPM} = 8 A		-	1.8	-	V	
0 "	at $V_R = 0 V$; f = 1 MHz		-	90	120	pF	
Capacitance	at V _R = 7.5 V; f = 1 MHz	C _D	-	35	-	pF	

ELECTRICAL CHARACTERISTICS GSOT24 ($T_{amb} = 25$ °C unless otherwise specified) between pin 3 and pin 1								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	24	V		
Reverse voltage	at I _R = 1 μA	V _R	24	-	-	V		
Reverse current	at V _R = 24 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	27	30	33	V		
	at I _{PP} = 1 A		-	34	41	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _C	-	41	47	V		
	at I _{PP} = 1 A		-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _F	-	1.4	-	V		
Orneriterer	at $V_R = 0 V$; f = 1 MHz	0	-	65	80	pF		
Capacitance	at V _R = 12 V; f = 1 MHz	CD	-	20	-	pF		

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6 For technical questions, contact: <u>ESDprotection@vishay.com</u> Document Number: 85807

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ELECTRICAL CHARACTERISTICS GSOT36 (T _{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	36	V		
Reverse voltage	at I _R = 1 µA	V _R	36	-	-	V		
Reverse current	at V _R = 36 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	39	43	47	V		
	at I _{PP} = 1 A	V	-	49	60	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 3.5 A	V _C	-	59	71	V		
Ferward elemping valtage	at I _{PP} = 1 A	N	-	1	1.2	V		
Forward clamping voltage	at $I_{PP} = I_{PPM} = 3.5 \text{ A}$	V _F	-	1.3	-	V		
0	at $V_R = 0 V$; f = 1 MHz	0	-	52	65	pF		
Capacitance	at V _R = 18 V; f = 1 MHz	CD	-	12	-	pF		

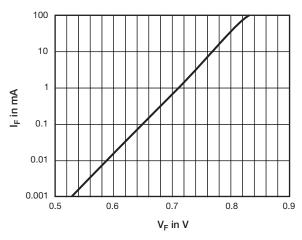


Fig. 1 - Typical Forward Current I_F vs. Forward Voltage V_F

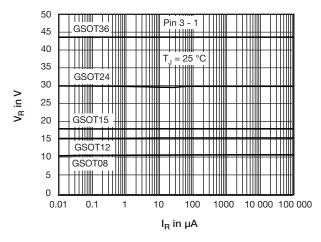


Fig. 2 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

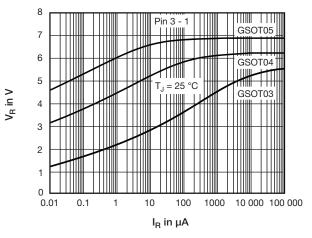


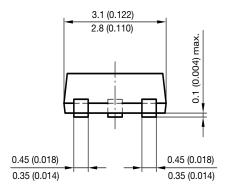
Fig. 3 - Typical Reverse Voltage V_R vs. Reverse Current I_R

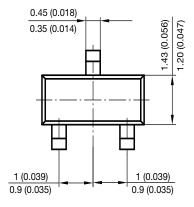
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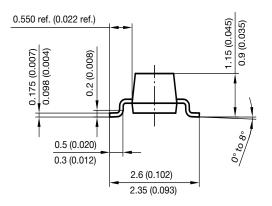


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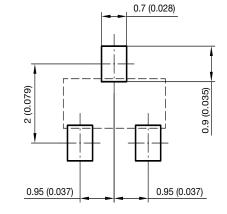
PACKAGE DIMENSIONS in millimeters (inches): SOT-23



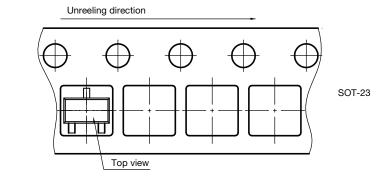




Foot print recommendation:



Document no.: 6.541-5014.01-4 Rev. 8 - Date: 23.Sept.2009 17418



Orientation in carrier tape SOT-23 S8-V-3929.01-006 (4) 04.02.2010 22607



Vishay

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